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Sheet \_ 2 (B) \_ of \_ 2 SUBSTITUTE FORM PTO-1449 ATTY, DOCKET NO. SERIAL NO. U.S. DEPARTMENT OF COMMERCE 10/797.876 PATENT AND TRADEMARK OFFICE **TPS-007** (MODIFIED) APPLICANT INFORMATION DISCLOSURE STATEMENT BY APPLICANT Anthony Dip et al. **GROUP** FILING DATE (Use several sheets if necessary) 2813 March 10, 2004 (37 CFR 1.98(b)) **U.S. PATENT DOCUMENTS** FILING DATE ISSUE EXAMINER IF APPROPRIATE CLASS **SUBCLASS** PATENT NUMBER **PATENTEE** INITIAL DATE B.A B.B B.C B.D B.E B.F B.G B.H B.I B.J B.K FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS TRANSLATION **PUBLICATION** COUNTRY OR DOCUMENT (YES/NO) **SUBCLASS** PATENT OFFICE **CLASS** NUMBER DATE B.L В.М B.N B.O В.Р B.Q OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication) Choi et al., Electrical Characteristics of ZrO, Gate Dielectric Deposited on Ultrathin Silicon Capping Layer for SiGe Metal-Oxide-Semiconductor Device Applications, Jpn. J. Appl. Physics, Part 1, Vol 41, No. 8, Aug 2002, pp. 5129-5130 B.R CAM Chatterjee et al., Electrical Properties of Stacked Gate Dielectric (SiO<sub>2</sub>/ZrO<sub>2</sub>) Deposited on Strained SiGe Layers, Thin Solid Films, Vol. 422, No. 1-2, 12/20/2002, pp. 33-38 B.S CAM European Patent Office, International Search Report, PCT/US2005/000661, Dated 7/27/2005, 5 pp. CAM B.T DATE CONSIDERED **EXAMINER** 

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